

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor light emitting device, comprising:  
a GaP substrate;  
an active layer located above said GaP substrate and including an n-type layer and a p-type layer of a compound semiconductor;  
an ELO layer located between said GaP substrate and said active layer and formed by epitaxial lateral growth; and  
a growth supporting layer located under and in contact with said ELO layer, wherein  
said ELO layer fills a window portion formed in said growth supporting layer, and grows  
laterally abutting on the growth supporting layer,  
the growth supporting layer comprises an SiO<sub>2</sub> layer, and  
the ELO layer comprises an AlGaAs layer.
2. (Cancelled)
3. (Withdrawn - Currently Amended) The semiconductor light emitting device according to claim [[2]] 1, comprising a buffer layer of the compound semiconductor on said GaP substrate, wherein said growth supporting layer is located on and in contact with the buffer layer, and said ELO layer fills said window portion so that said ELO layer is in contact with the buffer layer and grows abutting on said growth supporting layer.

4. (Currently Amended) The semiconductor light emitting device according to claim [[2]] 1, wherein said growth supporting layer is located in contact with said GaP substrate, said ELO layer fills said window portion so that said ELO layer is in contact with the substrate and grows abutting on said growth supporting layer.
5. (Currently Amended) The semiconductor light emitting device according to claim [[2]] 1, wherein said window portion is arranged linearly and/or in a broken line on both sides so as to sandwich a predetermined space, and has a pattern that is periodic in a plan view.
6. (Withdrawn - Currently Amended) The semiconductor light emitting device according to claim [[2]] 1, wherein in a plan view, said ELO layer is located to be encompassed by said window portion, and an electrode is arranged to surround said ELO layer encompassed by the window portion.
7. (Withdrawn - Currently Amended) The semiconductor light emitting device according to claim [[2]] 1, wherein in a plan view, said ELO layer is encompassed by said window portion and located so as to surround a partial region of said growth supporting layer, and an electrode is located on the partial region surrounded by the ELO layer.
8. (Cancelled)

9. (Withdrawn) The semiconductor light emitting device according to claim 1, wherein said GaP substrate is provided with a scratched trench, said ELO layer fills the scratched trench provided in said GaP substrate, and grows laterally abutting on the GaP substrate.

10. (Withdrawn) The semiconductor light emitting device according to claim 9, wherein said scratched trench is arranged linearly and/or in a broken line on both sides so as to sandwich the predetermined space and has a pattern that is periodic in a plan view.

11. (Cancelled)

12. (Previously Presented) The semiconductor light emitting device according to claim 1, wherein said ELO layer is formed through a liquid phase epitaxial growth.